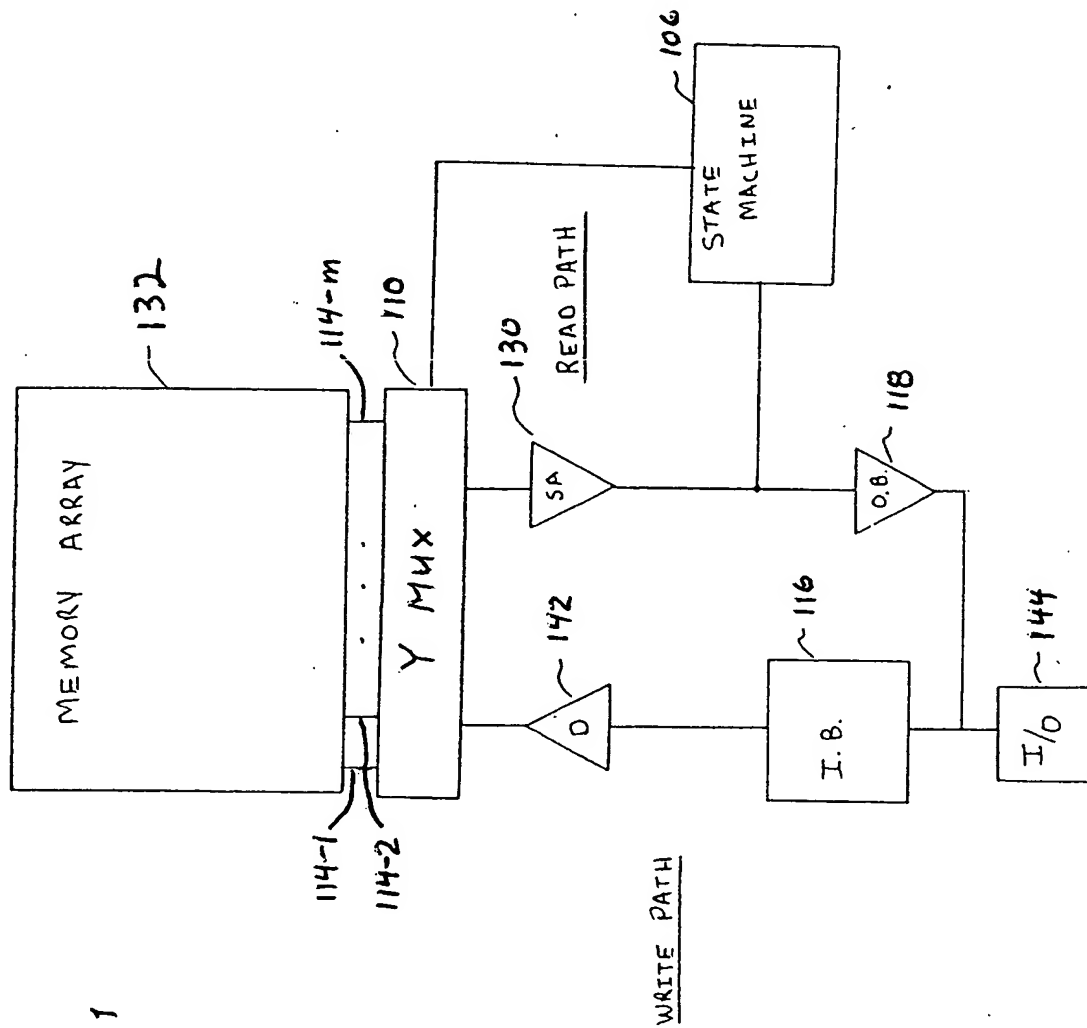


FIGURE 1
(PRIOR ART)



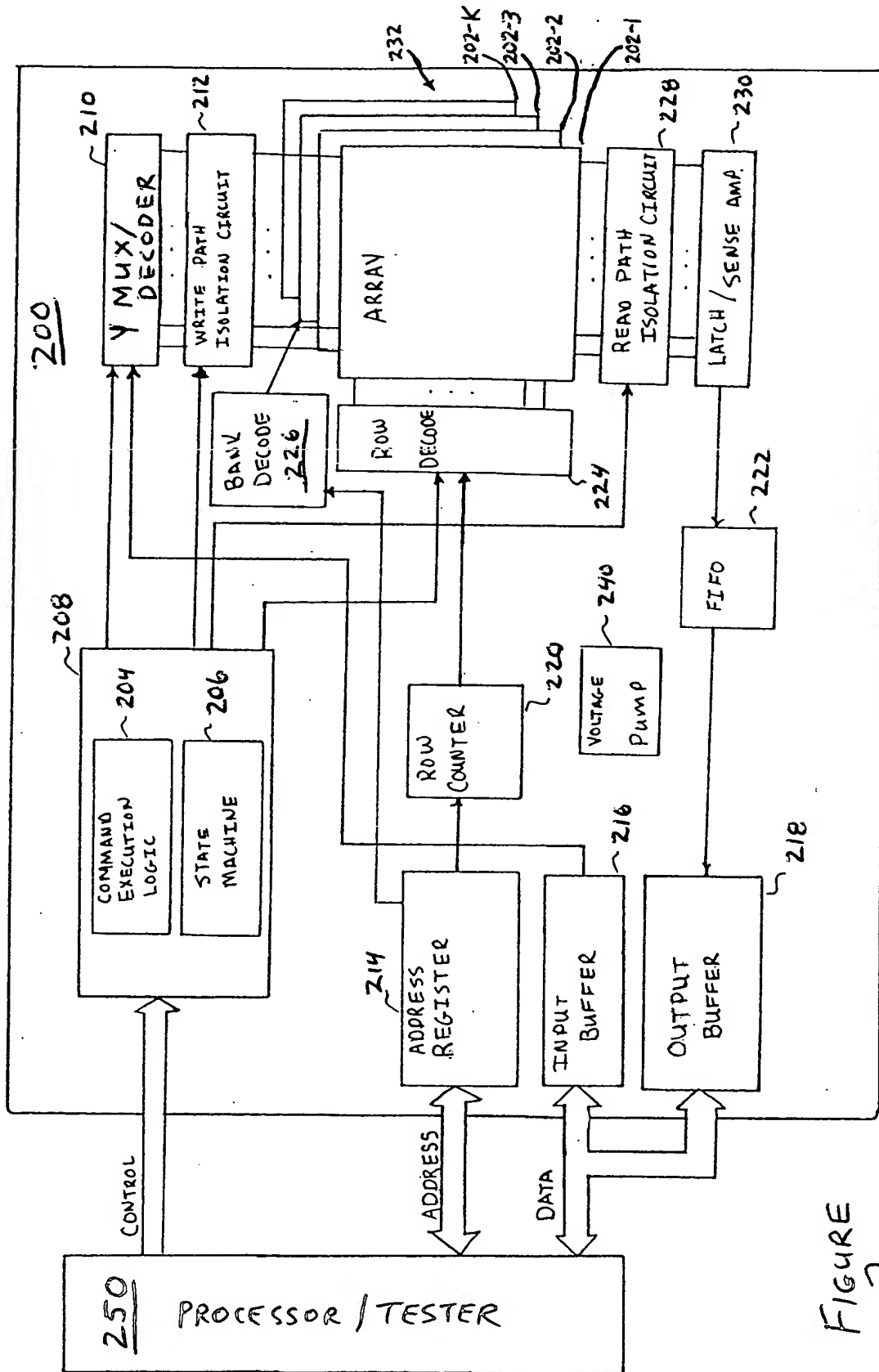
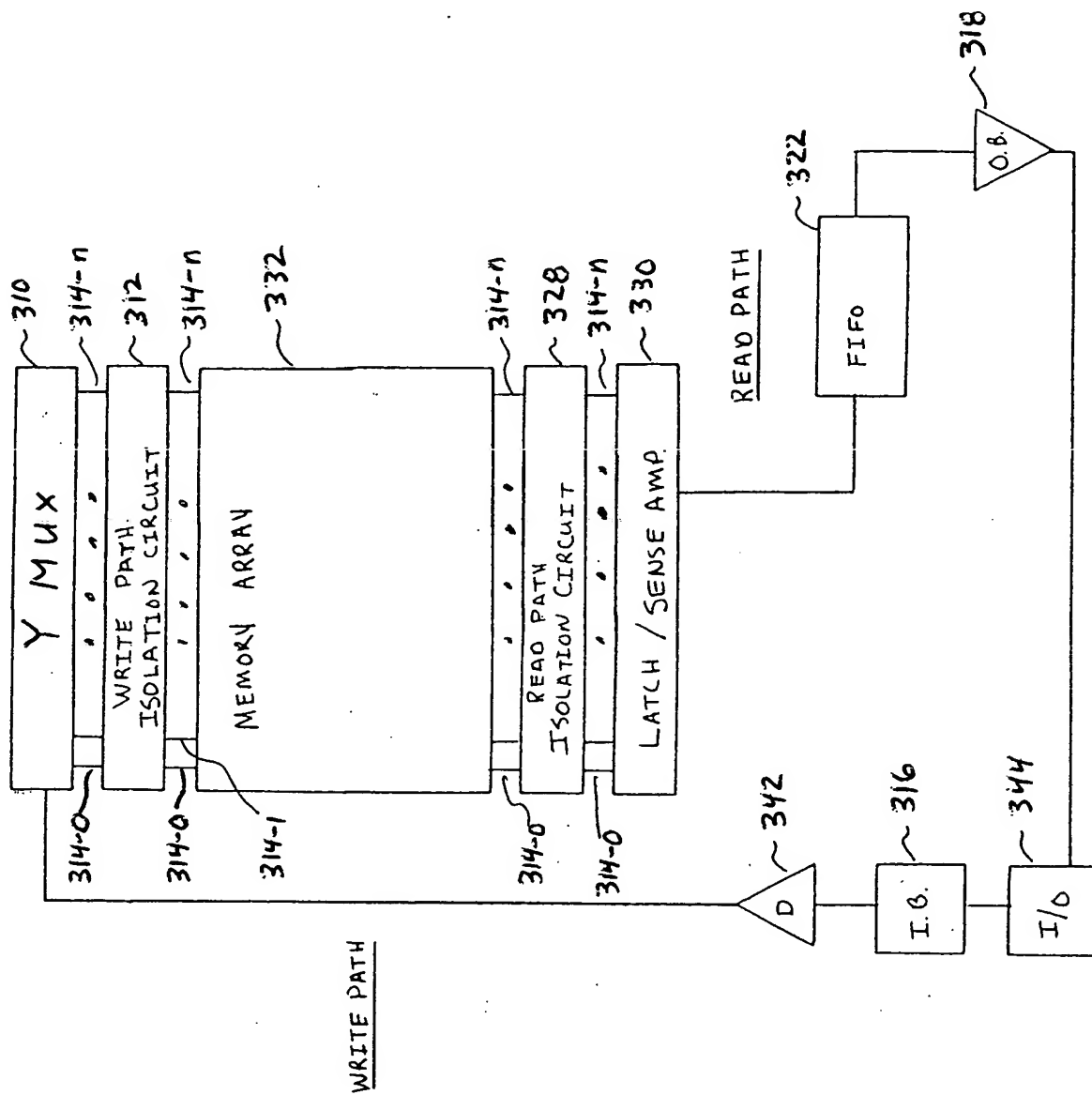


FIGURE 2

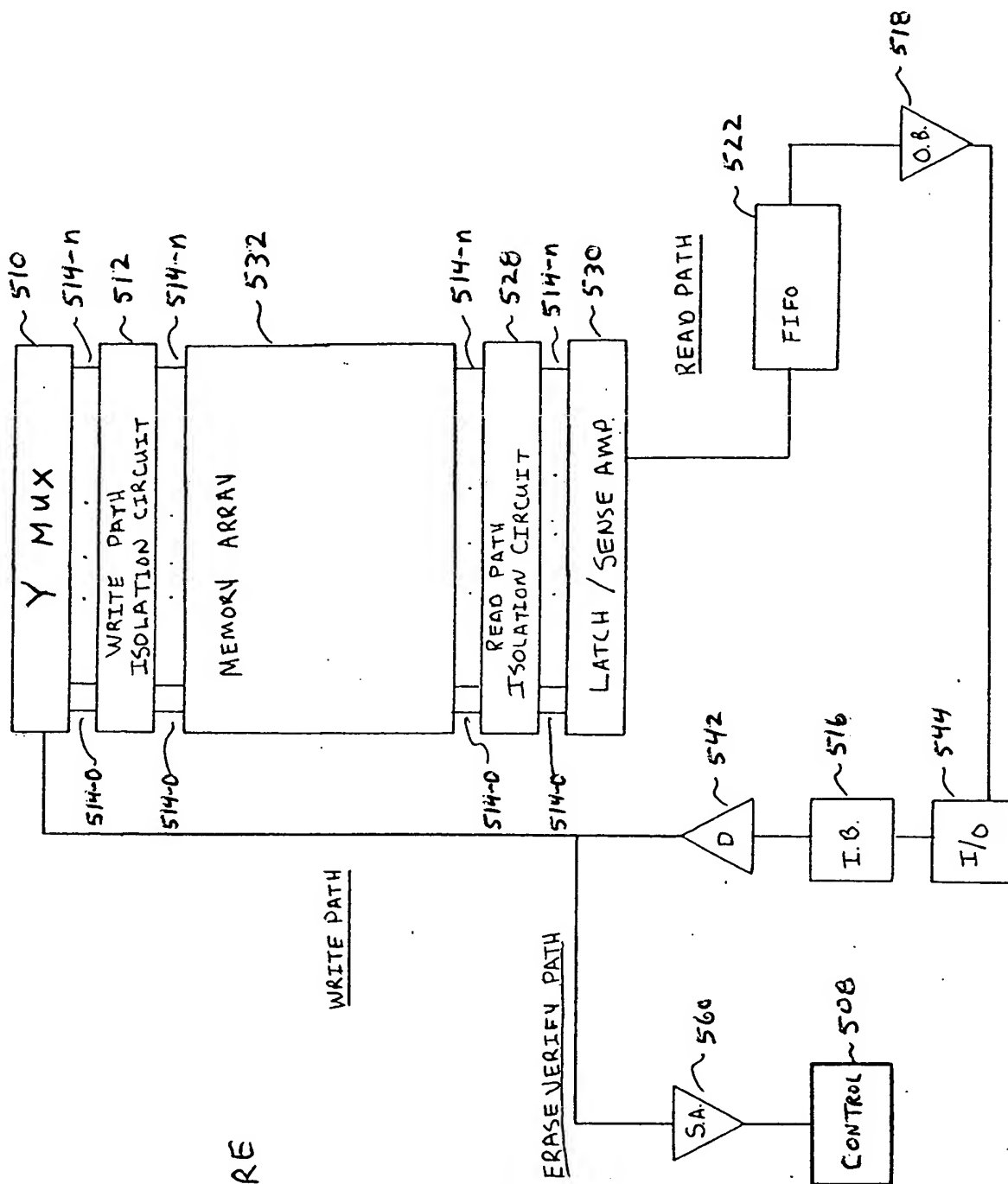
FIGURE
3



The schematic diagram illustrates a memory array architecture. At the top, a **Y Mux** (labeled 410) receives address signals $\sim 414-0, \sim 414-1, \dots, \sim 414-n$. Below it is the **WRITE PATH ISOLATION CIRCUIT** (labeled 412), which also receives these address signals. The main memory array consists of a grid of access transistors (labeled D) and storage capacitors (labeled S). The word lines are connected to the gates of the access transistors in the first column. The bit lines are connected to the gates of the access transistors in the second column. The data lines are connected to the gates of the access transistors in the third column. The array is connected to a **READ PATH ISOLATION CIRCUIT** (labeled 428) at the bottom, which also receives address signals $\sim 414-0, \sim 414-1, \dots, \sim 414-n$. Below the read path isolation circuit is the **LATCH/SENSE AMP** (labeled 430). The array is also connected to a **LATCH/SENSE AMP** (labeled 430) at the bottom. The array is connected to a **LATCH/SENSE AMP** (labeled 430) at the bottom. The array is connected to a **LATCH/SENSE AMP** (labeled 430) at the bottom.

FIGURE 4

FIGURE
5



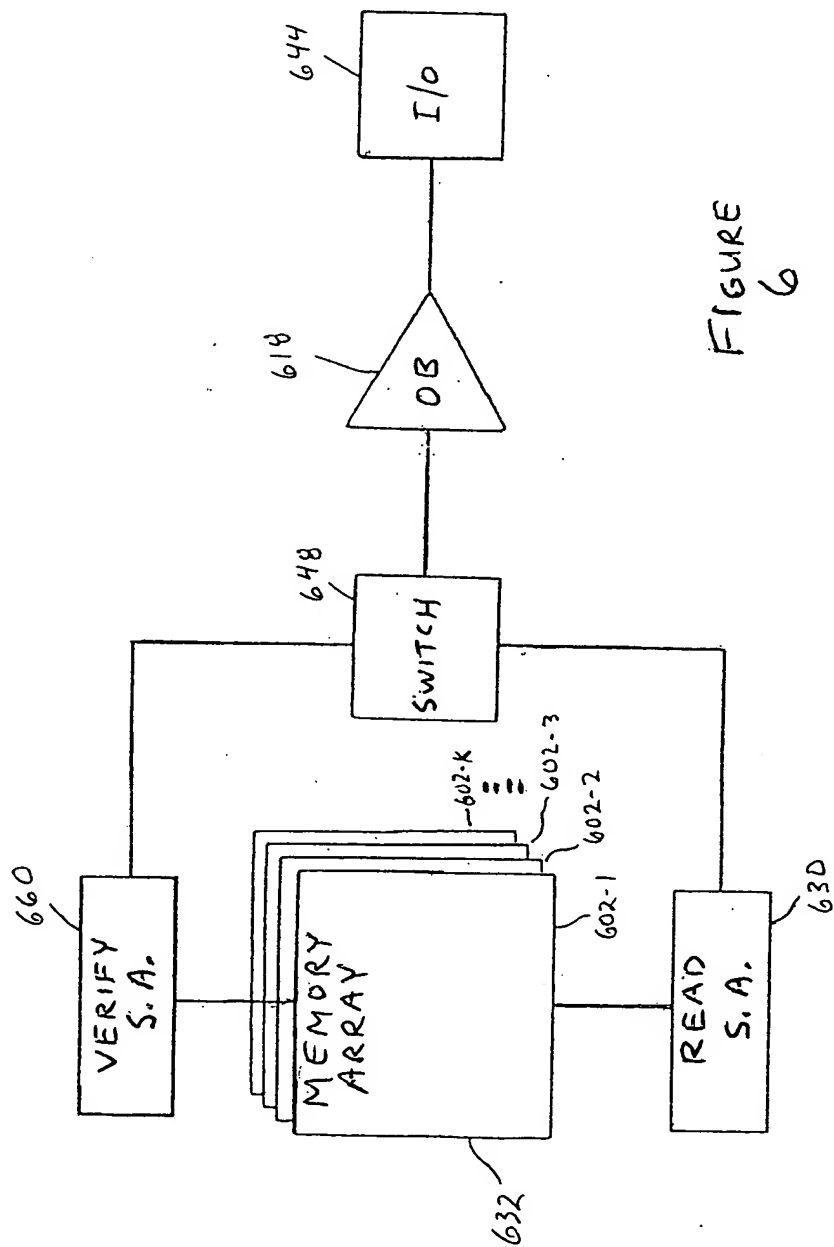


FIGURE 6

FIGURE 7

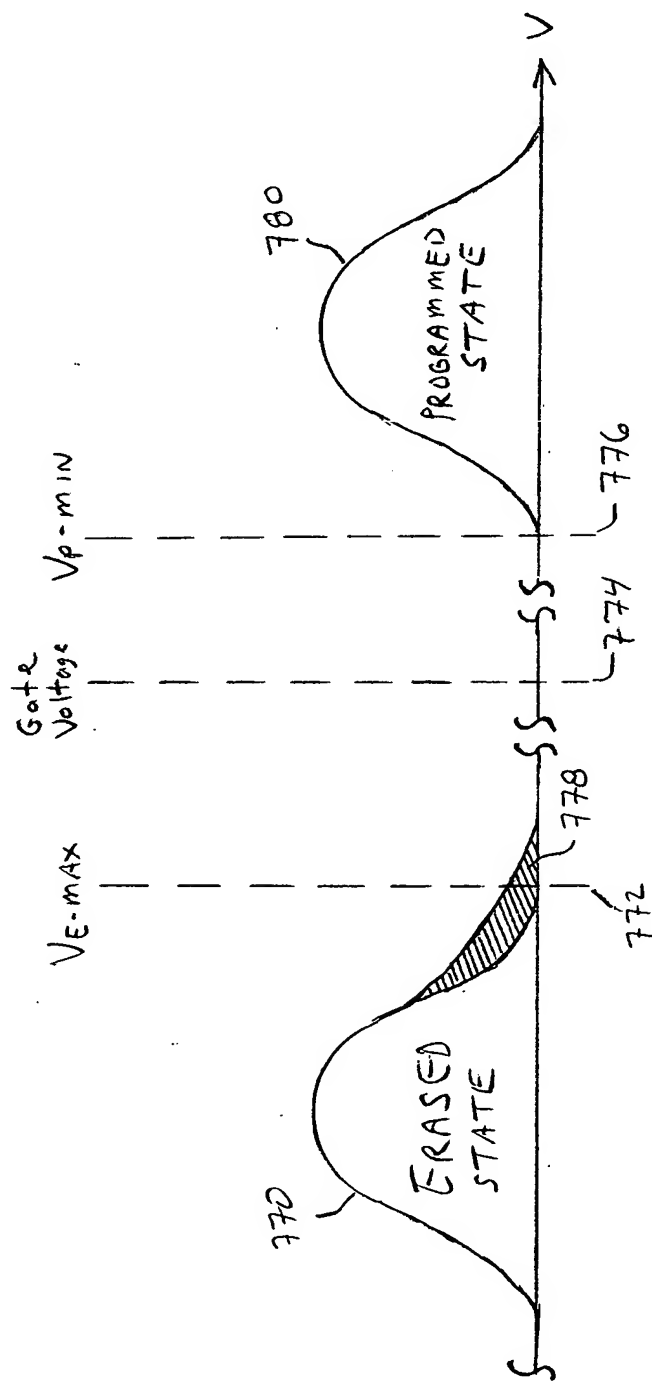


FIGURE 8
PRIOR ART

